

SOT-23 Plastic-Encapsulate DIODE

Features

• Power dissipation

 $P_D : 150 \text{ mW (T}_{amb}=25^{\circ}\text{C)}$

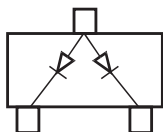
• Forward Current

 $I_F : 100 \text{ mA}$

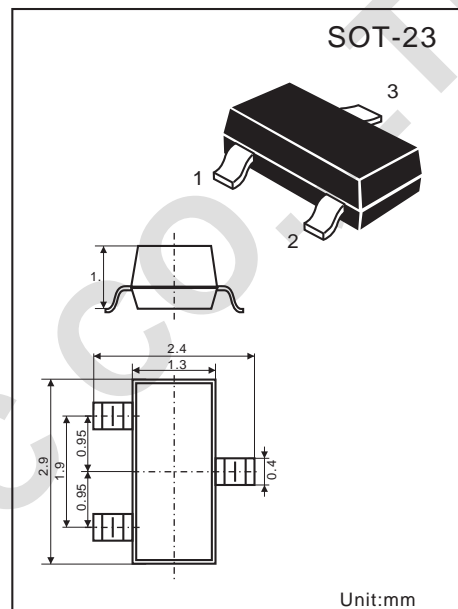
• Reverse Voltage

 $V_R : 80\text{V}$

• Operating and storage junction temperature range

 $T_j, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$ 

Marking:A3



ELECTRICAL CHARACTERISTICS

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	80		V
Reverse Voltage leakage current	I_R	$V_R=80\text{V}$		0.5	μA
Forward Voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode Capacitance	C_{tot}	$V_R=0\text{V}$ $f=1\text{MHz}$		4	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1I_R$		4	nS

